

## REMARKS

This Amendment is responsive to the Office Action dated May 19, 2005. Claims 1-23 were pending in the original application. In the Office Action, claims 1-23 were rejected. In this Amendment, claim 1 was amended and claims 21-22 were cancelled. Claims 1-20 and 23 thus remain for consideration.

Applicant submits that claims 1-20 and 23 are in condition for allowance and requests withdrawal of the rejections in light of the following remarks.

### Objection to the Drawings

The drawings were objected to because (1) of non-uniform (handwritten) numbering and labeling of the elements in the drawings and (2) the drawings must show every feature of the invention specified in the claims (See claims 21-23).

The drawings have been corrected and claims 21 and 22 have been cancelled, therefore, the above objections should be removed. Replacement drawings are attached to this amendment.

### §§ 103 Rejections

Claims 1-12 and 19-23 were rejected under 35 U.S.C. 103(a) as being unpatentable over Wong (U.S.P.N. 6,456,511) in view of Shmashita (U.S.P.N. 5,661,642).

Claims 13-18 were rejected under 35 U.S.C. 103(a) as being unpatentable over Wong (U.S.P.N. 6,456,511) in view of Shimashita (U.S.P.N. 5,661,642) as applied to claim 1 above, and further in view of Marziale (U.S.P.N. 6,239,988).

Applicant submits that independent claim 1 is patentable over Wong, Shimashita and Marziale -- taken either alone or in combination.

Applicant's invention as recited in the independent claims is directed toward a radiation tolerant electrical component for providing controlled electrical response in radiation-intensive applications. For example, independent claim 1 specifies that the electrical component comprises an input line, an output line, a drive circuit, a non-hardened p-channel FET, and an output rectification circuit. Claim 1 further specifies that when operating the electrical component in a radiation-intensive environment, the FET should operate at close to its maximum gate voltage signal thereby allowing the FET to function across a high range of radiation exposure. However, the FET will remain controllable even if the FET operates below its maximum gate voltage.

Wong, Shimashita and Marziale do not disclose operating an electrical component in a radiation-intensive environment whereby an FET of the electrical component operates at close to its maximum gate voltage signal thereby allowing the FET to function across a high range of radiation exposure with the FET remaining controllable even if the FET operates below its maximum gate voltage.

Since Wong, Shimashita and Marziale do not disclose operating an electrical component in a radiation-intensive environment whereby an FET of the electrical component operates at close to its maximum gate voltage signal thereby allowing the FET to function across a high range of radiation exposure with the FET remaining controllable even if the FET operates below its maximum gate voltage, Applicant believes that independent claim 1 is patentable over Wong, Shimashita and Marziale on at least this basis.

Claims 2-20 and 23 depend on claim 1. Since claim 1 is believed to be patentable over Wong, Shimashita and Marziale, claims 2-20 and 23 are believed to be patentable over Wong, Shimashita and Marziale on the basis of their dependency on claim 1.

**CONCLUSION**

Applicant respectfully submits that all of the claims now pending in the application are in condition for allowance, which action is earnestly solicited.

If any issues remain, or if the Examiner has any further suggestions, he/she is invited to call the undersigned at the telephone number provided below.

The Examiner is hereby authorized to charge any insufficient fees or credit any overpayment associated with the above-identified application to Deposit Account No. 06-0515.

Respectfully submitted,



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